X Wallart

List of Publications by Year
in descending order

29 papers	1,249 citations	394421 19 h-index	477307 29 g-index
29 all docs	29 docs citations	29 times ranked	1504 citing authors

#	Article	IF	Citations
1	Two-dimensional Rutherford-like scattering in ballistic nanodevices. Physical Review B, 2018, 98, .	3.2	3
2	NanoARPES of twisted bilayer graphene on SiC: absence of velocity renormalization for small angles. Scientific Reports, 2016, 6, 27261.	3.3	28
3	Formation of quantum dots in the potential fluctuations of InGaAs heterostructures probed by scanning gate microscopy. Physical Review B, 2015, 91, .	3.2	7
4	Probing the electronic properties of graphene on C-face SiC down to single domains by nanoresolved photoelectron spectroscopies. Physical Review B, 2015, 92, .	3.2	12
5	High-resolution angle-resolved photoemission spectroscopy study of monolayer and bilayer graphene on the C-face of SiC. Physical Review B, 2013, 88, .	3.2	22
6	Coherent tunnelling across a quantum point contact in the quantum Hall regime. Scientific Reports, 2013, 3, 1416.	3.3	26
7	Scanning gate spectroscopy of transport across a quantum Hall nano-island. New Journal of Physics, 2013, 15, 013049.	2.9	19
8	Transport Inefficiency in Branched-Out Mesoscopic Networks: An Analog of the Braess Paradox. Physical Review Letters, 2012, 108, 076802.	7.8	44
9	On the imaging of electron transport in semiconductor quantum structures by scanning-gate microscopy: successes and limitations. Semiconductor Science and Technology, 2011, 26, 064008.	2.0	73
10	High yield of self-catalyzed GaAs nanowire arrays grown on silicon via gallium droplet positioning. Nanotechnology, 2011, 22, 275602.	2.6	146
11	Graphene growth by molecular beam epitaxy using a solid carbon source. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 300-303.	1.8	86
12	Graphene growth by molecular beam epitaxy on the carbon-face of SiC. Applied Physics Letters, 2010, 97, .	3.3	80
13	Gold-free GaAs/GaAsSb heterostructure nanowires grown on silicon. Applied Physics Letters, 2010, 96, .	3.3	83
14	Imaging Coulomb islands in a quantum Hall interferometer. Nature Communications, 2010, 1, 39.	12.8	60
15	Atomic scale flattening, step formation and graphitization blocking on 6H- and 4H-SiC{0 0 0 1} surfaces under Si flux. Semiconductor Science and Technology, 2009, 24, 125014.	2.0	20
16	Comparative Sb and As segregation at the InP on GaAsSb interface. Applied Physics Letters, 2008, 93, .	3.3	9
17	Kinetics, stoichiometry, morphology, and current drive capabilities of Ir-based silicides. Journal of Applied Physics, 2007, 102, .	2.5	11
18	Imaging Electron Wave Functions Inside Open Quantum Rings. Physical Review Letters, 2007, 99, 136807.	7.8	65

#	Article	IF	Citations
19	Imaging and controlling electron transport inside a quantum ring. Nature Physics, 2006, 2, 826-830.	16.7	73
20	Dwell-Time-Limited Coherence in Open Quantum Dots. Physical Review Letters, 2005, 94, 146802.	7.8	47
21	Transmission electron microscopy of iridium silicide contacts for advanced MOSFET structures with Schottky source and drain. Journal of Alloys and Compounds, 2004, 382, 24-28.	5.5	1
22	Formation of platinum-based silicide contacts: Kinetics, stoichiometry, and current drive capabilities. Journal of Applied Physics, 2003, 94, 7801.	2.5	76
23	Long dephasing time and high-temperature conductance fluctuations in an open InGaAs quantum dot. Physical Review B, 2002, 66, .	3.2	27
24	XPS study of GaInP on GaAs interface. Applied Surface Science, 1998, 123-124, 523-527.	6.1	3
25	X-ray photoemission characterization of interface abruptness and band offset of Ga0.5In0.5P grown on GaAs. Journal of Applied Physics, 1998, 84, 2127-2132.	2.5	26
26	Kinetics and mechanism of low temperature atomic oxygen-assisted oxidation of SiGe layers. Journal of Applied Physics, 1998, 83, 2842-2846.	2.5	27
27	Plasma assisted oxidation of SiGe layers at 500Â°C: interface characterization. Applied Surface Science, 1996, 104-105, 385-391.	6.1	8
28	Germanium behaviour during the low-temperature plasma-assisted oxidation of SiGe alloys. Surface and Interface Analysis, 1995, 23, 363-366.	1.8	3
29	Kinetic model of element III segregation during molecular beam epitaxy of IIIâ€IIIâ€™â€V semiconductor compounds. Applied Physics Letters, 1995, 66, 52-54.	3.3	164